



		ATTY. DOCKET NO.:	APPLICATION NO.:
		4717-13300	10/809,918
		APPLICANT:	
		C. Maleville et al.	
		FILING DATE:	GROUP:
		March 26, 2004	2812 2824

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BEO	AA	4,743,767	5/1988	Plumb et al.	250	492.2	
BEO	AB	4,751,393	6/1988	Corey, Jr. et al.	250	492.21	
BEO	AC	4,807,994	2/1989	Felch et al.	356	326	
BEO	AD	5,374,564	12/1994	Bruel	437	24	
	AE	5,834,463	11/1998	Ohkawa et al.	514	220	
BEO	AF	5,998,798	12/1999	Halling et al.	250	492.21	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AG							
	AH							
	AI							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

BEO	AJ	Scott M. Baumann, "Rutherford Backscattering Spectrometry (RBS), Charles Evans & Associates, Specialists in Materials Characterization, pp. 1-15.
	AK	
	AL	
	AM	
	AN	
	AO	

EXAMINER	DATE CONSIDERED
Beth E. Owens	9.13-04

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

		ATTY DOCKET NO 4717-1330U	APPLICATION NO 10/809,918
APPLICANT C. Maleville et al.			
FILING DATE March 26, 2004		GROUP 2812	

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
BEO	AA	760 409	6/1998	Chen et al.	250	492.21	
	AB	BEO 9.17.04					
	AC						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							VIS	NO
BEO	AD	JP 61 043417 A English Abstract	3/1986	Japan 250			X	
BEO	AE	WO 99 08307 A	2/1999	PCT			X	
	AF							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc)

BEO	AG	Shuettekate et al., XP004195210, "Dose and implantation temperature influence extended defects nucleon in c-Si", Nuclear instruments and methods in physics research, section B: beam interactions with materials and atoms, North-Holland Publishing Company, Vol. 164-165, pp. 425-430 (2000)
BEO	AH	L.J. Huang et al., XP000905645, "Model for blistering of hydrogen implanted silicon and its application to silicon-on-quartz", Electrochemical Society Proceedings, Processing of 8th International Symposium on Semiconductor Silicon Vol 98-1, pp. 1373-1384 (1998)
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BEO	AK	Lanzieri et al., XP000073904 "Activation Uniformity Improvement of Undoped semi-insulating Gaas with an improved Post-Implant Anneal Furnace", Journal of applied Physics, New York, Vol. 66, No. 8, pp 3643-3644 (1989) BEO 9.17.04

EXAMINER	DATE CONSIDERED
Beth E. Owens	9.17.04